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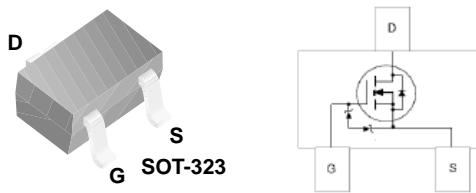
May 2011

## 2N7002KW

### N-Channel Enhancement Mode Field Effect Transistor

#### Features

- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Ultra-Small Surface Mount Package
- Pb Free/RoHS Compliant
- ESD HBM=1000V as per JESD22 A114 and ESD CDM=1500V as per JESD22 C101



Marking : 7KW

#### Absolute Maximum Ratings \* $T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Value	Units
$V_{DSS}$	Drain-Source Voltage	60	V
$V_{GSS}$	Gate-Source Voltage	$\pm 20$	V
$I_D$	Maximum Drain Current - Continuous $T_J = 100^\circ\text{C}$ - Pulsed	310 195 1.2	mA mA A
$T_J$	Operating Junction Temperature Range	-55 to +150	$^\circ\text{C}$
$T_{STG}$	Storage Temperature Range	-55 to +150	$^\circ\text{C}$

\* These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

#### Thermal Characteristics

Symbol	Parameter	Value	Units
$P_D$	Total Device Dissipation Derating above $T_A = 25^\circ\text{C}$	300 2.4	mW mW/ $^\circ\text{C}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient *	410	$^\circ\text{C}/\text{W}$

\* Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch. Minimum land pad size

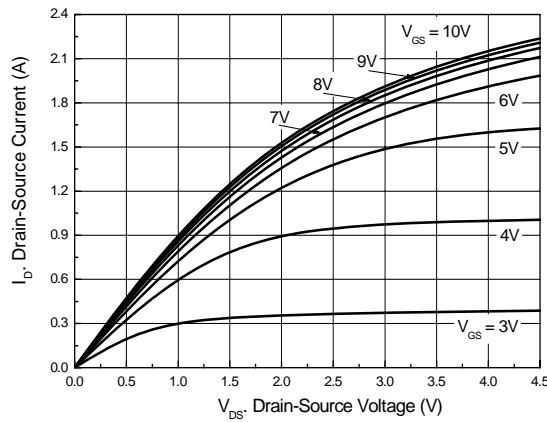
**Electrical Characteristics**  $T_A = 25^\circ\text{C}$  unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
<b>Off Characteristics</b>						
$BV_{DSS}$	Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 10\mu\text{A}$	60			V
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS} = 60V, V_{GS} = 0V$ $V_{DS} = 60V, V_{GS} = 0V, T_J = 125^\circ\text{C}$			1.0 0.5	$\mu\text{A}$ mA
$I_{GSS}$	Gate-Body Leakage	$V_{GS} = \pm 20V, V_{DS} = 0V$			$\pm 10$	$\mu\text{A}$
<b>On Characteristics</b> (Note1)						
$V_{GS(\text{th})}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\mu\text{A}$	1.1		2.1	V
$R_{DS(\text{ON})}$	Static Drain-Source On-Resistance	$V_{GS} = 10V, I_D = 500\text{mA}$ $V_{GS} = 10V, I_D = 500\text{mA}, T_J = 100^\circ\text{C}$ $V_{GS} = 5V, I_D = 50\text{mA}$ $V_{GS} = 5V, I_D = 50\text{mA}, T_J = 100^\circ\text{C}$			1.6 2.4 2 3	$\Omega$ $\Omega$ $\Omega$ $\Omega$
$V_{DS(\text{ON})}$	Drain-Source On-Voltage	$V_{GS} = 10V, I_D = 500\text{mA}$ $V_{GS} = 5V, I_D = 50\text{mA}$			3.75 1.5	V V
$I_{D(\text{ON})}$	On-State Drain Current	$V_{GS} = 10V, V_{DS} = 2V$	500			mA
$g_{FS}$	Forward Transconductance	$V_{DS} = 2V, I_D = 0.2\text{A}$	80			mS
<b>Dynamic Characteristics</b>						
$C_{iss}$	Input Capacitance	$V_{DS} = 25V, V_{GS} = 0V, f = 1.0\text{MHz}$			50	pF
$C_{oss}$	Output Capacitance				25	pF
$C_{rss}$	Reverse Transfer Capacitance				5	pF
<b>Switching Characteristics</b>						
$t_{D(\text{ON})}$	Turn-On Delay Time	$V_{DD} = 30V, R_L = 150\Omega, V_{GS} = 10V,$ $I_D = 200\text{mA}, R_{\text{GEN}} = 25\Omega$			20	ns
$t_{D(\text{OFF})}$	Turn-Off Delay Time				60	ns
<b>Drain-Source Diode Characteristics and Maximum Ratings</b>						
$I_S$	Maximum Continuous Drain-Source Diode Forward Current				115	mA
$I_{SM}$	Maximum Pulsed Drain-Source Diode Forward Current				0.8	A
$V_{SD}$	Drain-Source Diode Forward Voltage	$V_{GS} = 0V, I_S = 115\text{mA}$			1.1	V

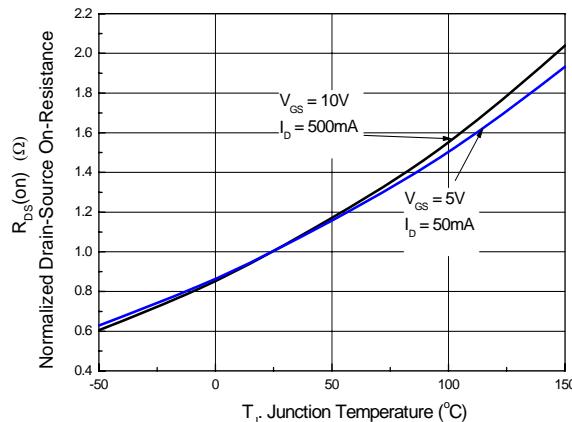
Note1 : 1. Pulse Test: Pulse Width < 300 $\mu\text{s}$ , Duty Cycle < 2.0%.

## Typical Performance Characteristics

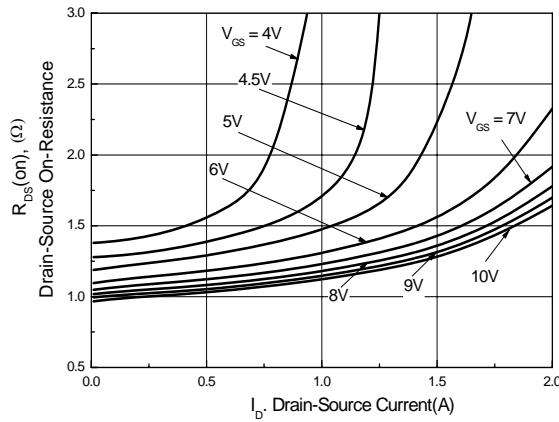
**Figure 1. On-Region Characteristics.**



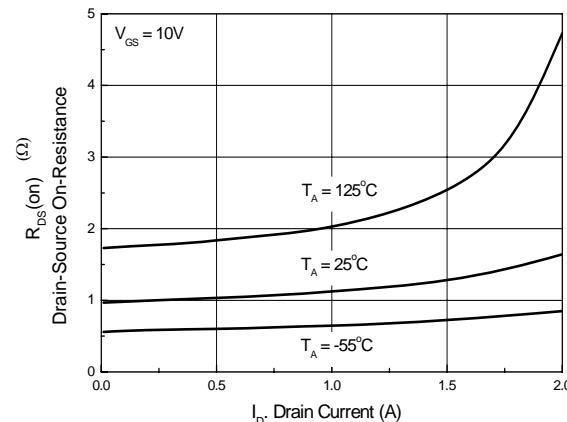
**Figure 2. On-Resistance Variation with Temperature.**



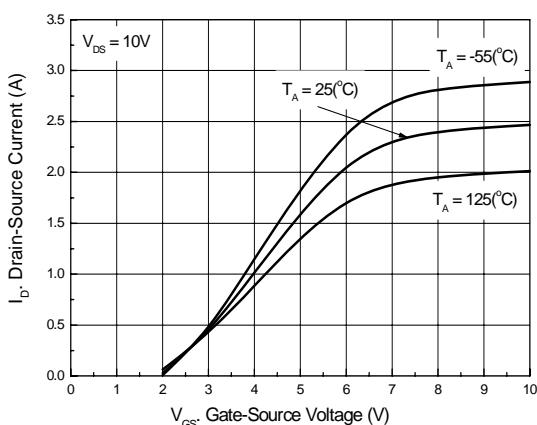
**Figure 3. On-Resistance Variation with Gate Voltage and Drain Current.**



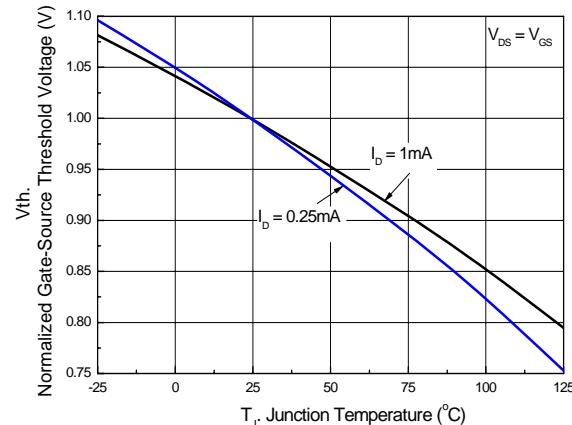
**Figure 4. On-Resistance Variation with Drain Current and Temperature.**



**Figure 5. Transfer Characteristics**

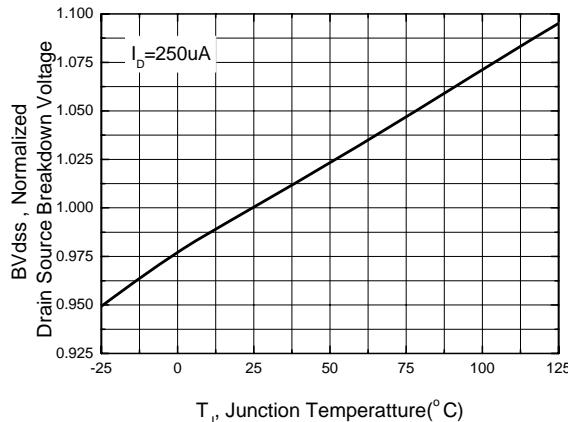


**Figure 6. Gate Threshold Variation with Temperature.**

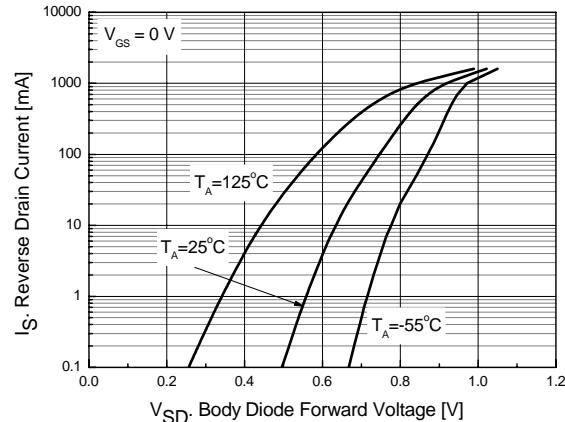


## Typical Performance Characteristics (Continued)

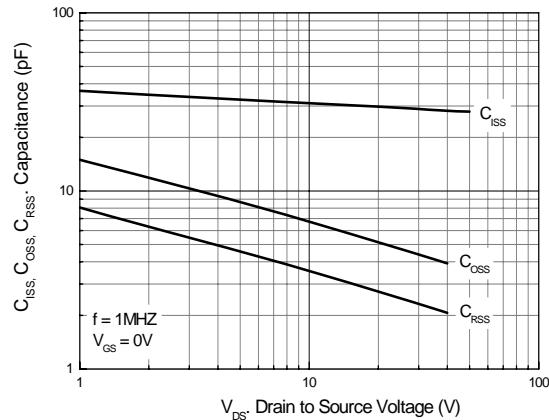
**Figure 7. Breakdown Voltage Variation with Temperature**



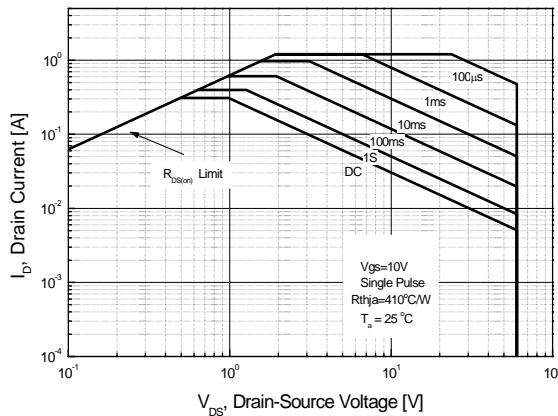
**Figure 8. Body Diode Forward Voltage Variation with Source Current and Temperature.**



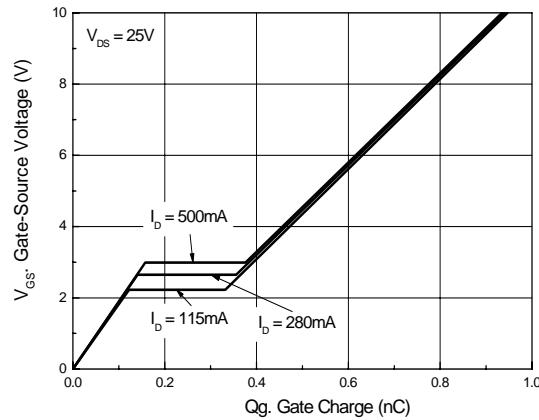
**Figure 9. Capacitance Characteristics.**



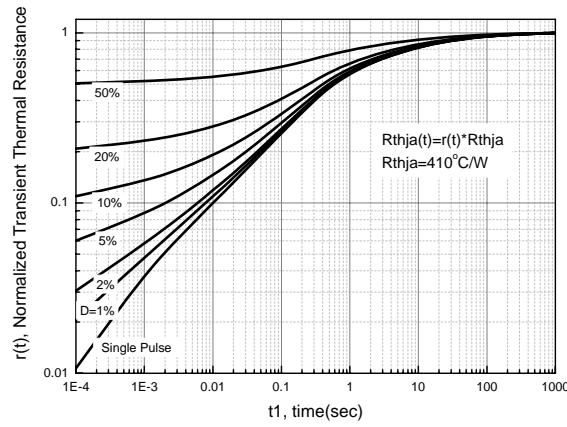
**Figure 11. Maximum Safe Operating Area.**



**Figure 10. Gate Charge Characteristics.**

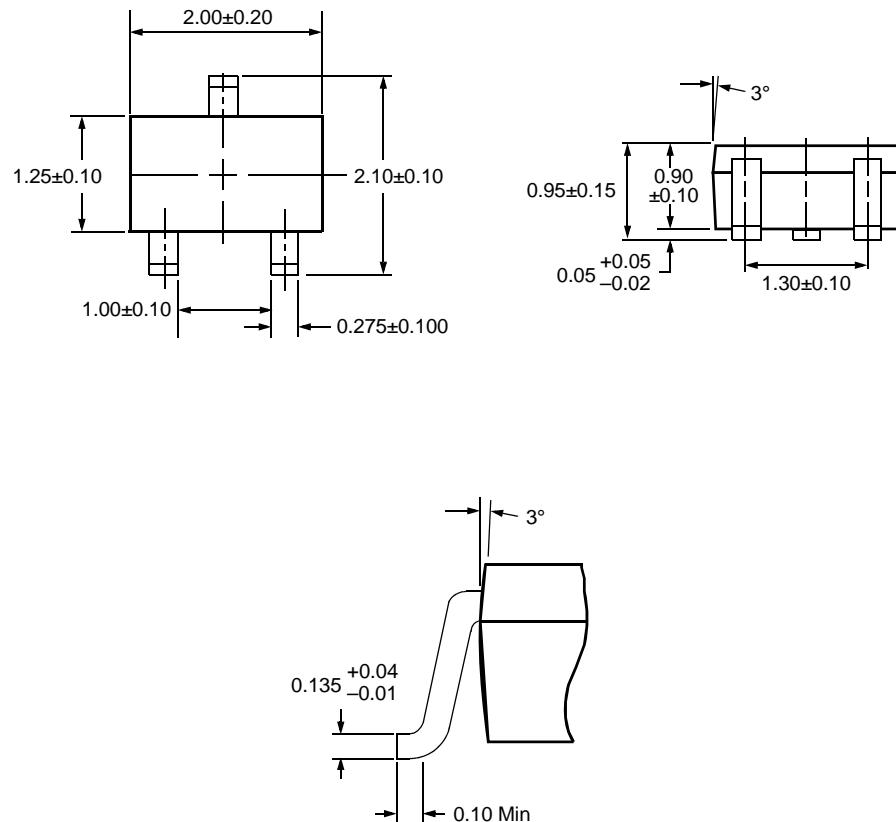


**Figure 12. Transient Thermal Response Curve.**



## Physical Dimensions

**SOT-323**



Dimensions in Millimeters



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